

PWM OUTPUT TEMPERATURE SENSOR IC

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Rev.1.2_01

The S-5855A Series, developed by CMOS technology, is a 1-wire PWM output temperature sensor IC of low current consumption that itself changes the duty ratio according to temperature.

The duty ratio decreases from 100% if exceeding the temperature set by user, and this decrease is linear against the temperature rise.

The output form is selectable from CMOS output and Nch open-drain output.

Its small packages SNT-4A and SOT-23-5 enable high-density mounting.

■ Features

- | | |
|---------------------------------------|---|
| • PWM output | : 1-wire PWM interface |
| • Temperature accuracy | : $\pm 3.0^{\circ}\text{C}$ |
| • Duty ratio change-start temperature | : Selectable from $+40^{\circ}\text{C}$ to $+80^{\circ}\text{C}$ in 10°C step |
| • Duty ratio temperature sensitivity | : Selectable from $-1\ \%/^{\circ}\text{C}$ to $-4\ \%/^{\circ}\text{C}$ in $1\ \%/^{\circ}\text{C}$ step |
| • Low current consumption | : $50\ \mu\text{A}$ typ. ($T_a = +25^{\circ}\text{C}$) |
| • Low power supply voltage | : 1.65 V to 5.5 V |
| • Wide range of operation temperature | : $T_a = -40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$ |
| • Lead-free (Sn 100%), halogen-free | |

■ Application

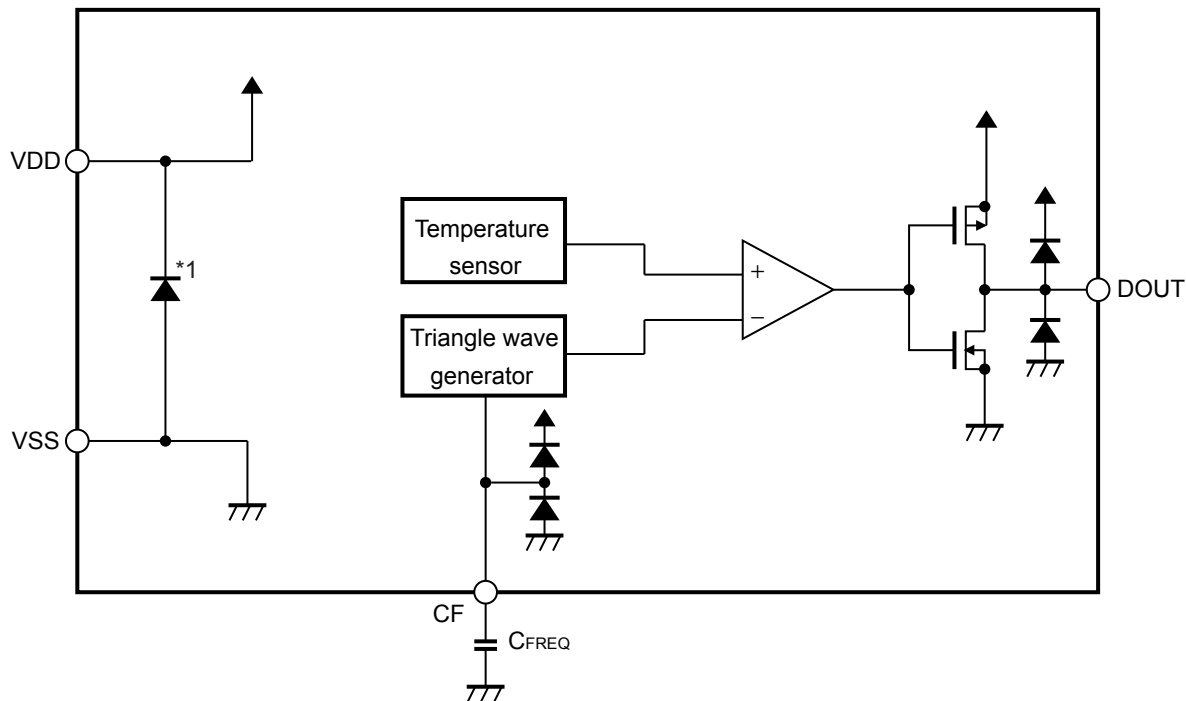
- Temperature compensation for LED instruments

■ Packages

- SNT-4A
- SOT-23-5

■ Block Diagrams

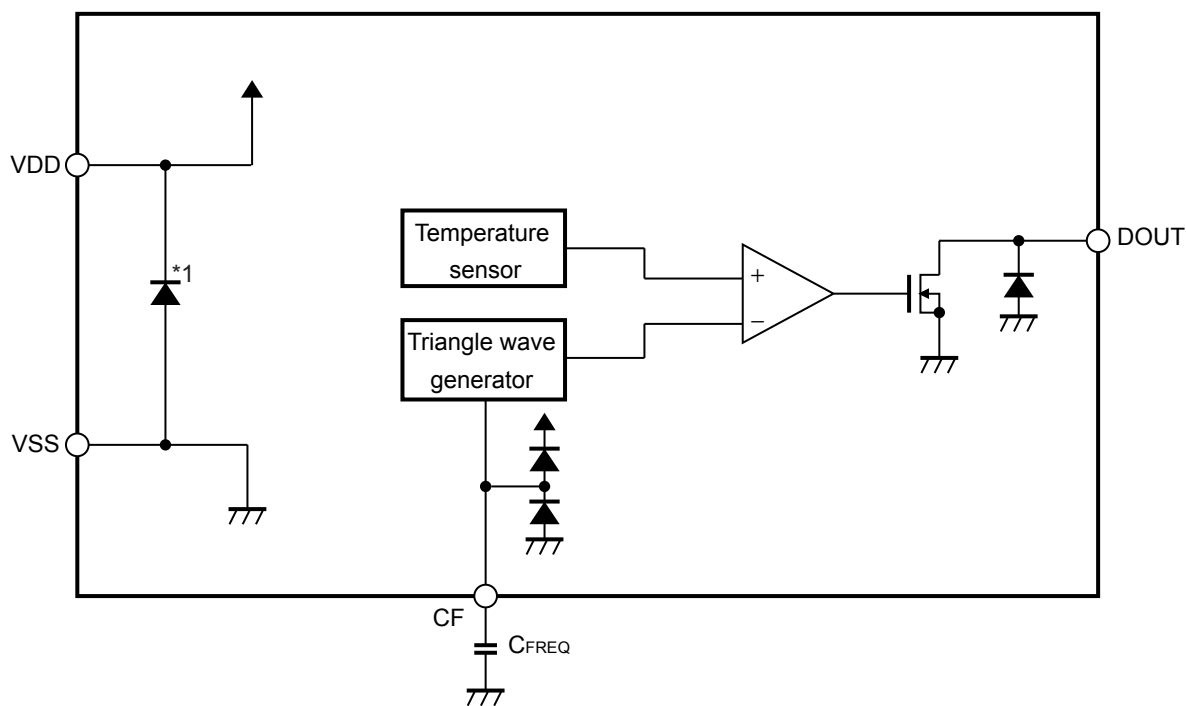
1. CMOS output product



*1. Parasitic diode

Figure 1

2. Nch open-drain output product

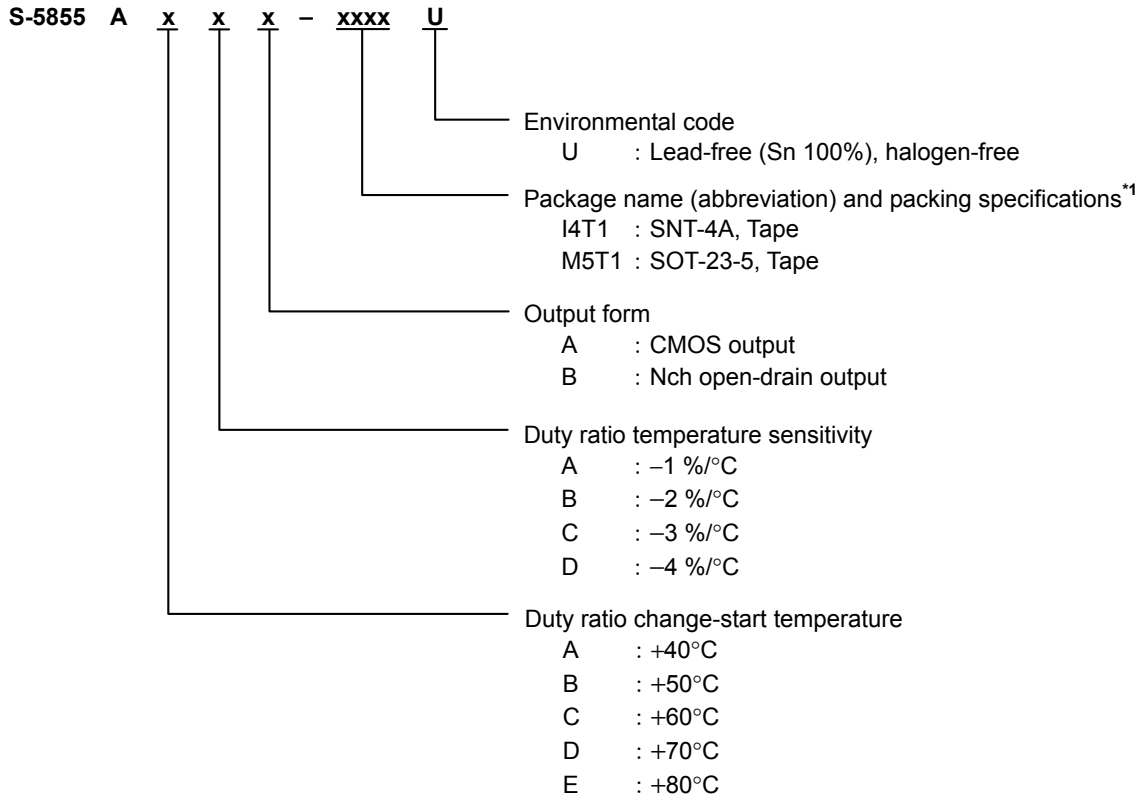


*1. Parasitic diode

Figure 2

■ Product Name Structure

1. Product name



*1. Refer to the tape drawing.

2. Packages

Package Name	Drawing Code			
	Package	Tape	Reel	Land
SNT-4A	PF004-A-P-SD	PF004-A-C-SD	PF004-A-R-SD	PF004-A-L-SD
SOT-23-5	MP005-A-P-SD	MP005-A-C-SD	MP005-A-R-SD	-

3. Product name list

(1) SNT-4A

Table 1

Product name	Duty ratio change-start temperature T_s^{*1} [°C]	Duty ratio temperature sensitivity $Ddt(s)^{*2}$ [%/°C]	Output form	T_{SP5}^{*3} [°C]	T_{EM5}^{*4} [°C]
S-5855AACA-I4T1U	+40	-3	CMOS output	+45	+60
S-5855AEAA-I4T1U	+80	-1	CMOS output	+85	+125
S-5855AECA-I4T1U	+80	-3	CMOS output	+85	+100

- *1. T_s : Duty ratio change-start temperature set by user
- *2. $Ddt(s)$: Duty ratio temperature sensitivity set by user
- *3. T_{SP5} : Temperature 5°C higher than duty ratio change-start temperature T_s (Refer to **Table 12** for details)
- *4. T_{EM5} : Higher temperature when measuring duty ratio temperature sensitivity (Refer to **Table 12** for details)

Remark Please contact our sales office for products other than those specified above.

(2) SOT-23-5

Table 2

Product name	Duty ratio change-start temperature T_s^{*1} [°C]	Duty ratio temperature sensitivity $Ddt(s)^{*2}$ [%/°C]	Output form	T_{SP5}^{*3} [°C]	T_{EM5}^{*4} [°C]
S-5855AAAA-M5T1U	+40	-1	CMOS output	+45	+115
S-5855AAAB-M5T1U	+40	-1	Nch open-drain output	+45	+115
S-5855AADA-M5T1U	+40	-4	CMOS output	+45	+55

- *1. T_s : Duty ratio change-start temperature set by user
- *2. $Ddt(s)$: Duty ratio temperature sensitivity set by user
- *3. T_{SP5} : Temperature 5°C higher than duty ratio change-start temperature T_s (Refer to **Table 12** for details)
- *4. T_{EM5} : Higher temperature when measuring duty ratio temperature sensitivity (Refer to **Table 12** for details)

Remark Please contact our sales office for products other than those specified above.

■ Pin Configurations

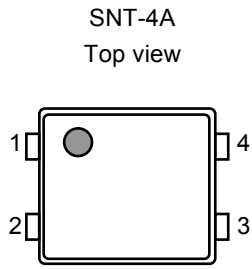


Figure 3

Table 3

Pin No.	Symbol	Pin Description
1	VSS	GND pin
2	CF	Connection pin for frequency control capacitor
3	VDD	Power supply pin
4	DOUT	Output pin

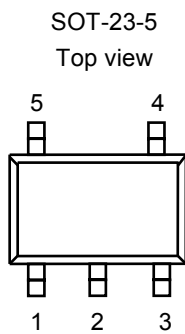


Figure 4

Table 4

Pin No.	Symbol	Pin Description
1	CF	Connection pin for frequency control capacitor
2	VSS	GND pin
3	NC*1	No connection
4	DOUT	Output pin
5	VDD	Power supply pin

*1. The NC pin is electrically open.
The NC pin can be connected to VDD pin or VSS pin.

■ Absolute Maximum Ratings

Table 5

(Ta = +25°C, V_{SS} = 0 V, unless otherwise specified)

Item	Symbol	Absolute Maximum Rating	Unit
Power supply voltage	V _{DD}	V _{SS} -0.3 to V _{SS} +7.0	V
Output voltage	V _{OUT}	CMOS output product	V _{SS} -0.3 to V _{DD} +0.3
		Nch open-drain output product	V _{SS} -0.3 to V _{SS} +7.0
CF voltage	V _{CF}	V _{SS} -0.3 to V _{DD} +0.3	V
Output current	I _{OUT}	-13 to +13	mA
Power dissipation	P _D	SNT-4A	300*1
		SOT-23-5	600*1
Operating ambient temperature	T _{opr}	-40 to +125	°C
Storage temperature	T _{stg}	-65 to +150	°C

*1. When mounted on board
[Mounted board]

(1) Board size: 114.3 mm × 76.2 mm × t1.6 mm

(2) Name: JEDEC STANDARD51-7

Caution The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

■ Electrical Characteristics

1. Common items

Table 6

(Ta = T_{SP5}, V_{DD} = 3.0 V, V_{SS} = 0 V, unless otherwise specified)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit	Test circuit	
Power supply voltage	V _{DD}	–	1.65	–	5.5	V	1	
Current consumption	I _{DD}	No load at output pin	Ta = T _{SP5}	–	–	200	μA	1
			Ta = +25°C (Duty ratio 100%)	–	50	–	μA	1
Output leakage current	I _{LEAK}	Nch open-drain output product V _{OUT} = 5.5 V, Ta = +25°C	–	–	1	μA	3	
Output source current	I _{SOURCE}	CMOS output product V _{OUT} = V _{DD} – 0.3 V	0.8	–	–	mA	3	
Output sink current	I _{SINK}	V _{OUT} = V _{SS} + 0.3 V	3	–	–	mA	3	
Fall time	t _F	C _L = 100 pF, R _L = 10 kΩ V _{OUT} = 0.8 × V _{DD} to 0.2 × V _{DD}	Nch open-drain output product	–	20	–	ns	5
			CMOS output product	–	20	–	ns	4
Rise time	t _R	C _L = 15 pF, R _L = 10 kΩ V _{OUT} = 0.2 × V _{DD} to 0.8 × V _{DD}	Nch open-drain output product	–	300	–	ns	5
			CMOS output product C _L = 100 pF, R _L = 10 kΩ V _{OUT} = 0.2 × V _{DD} to 0.8 × V _{DD}	–	50	–	ns	4

2. Product with duty ratio temperature sensitivity $Ddt(s) = -1 \%/^{\circ}C$

Table 7

($T_a = T_{SP5}$, $V_{DD} = 3.0 V$, $V_{SS} = 0 V$, $C_{FREQ} = 2.2 nF$, unless otherwise specified)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit	Test circuit
Duty ratio accuracy	Dsp5	$V_{DD} = 3.0 V$	92.0	95.0	98.0	%	2
		$V_{DD} = 1.65 V$ to $5.5 V$	91.0	95.0	99.0	%	2
Duty ratio temperature sensitivity	Ddt(E) ^{*1}	$T_a = T_{SP5}^{*2}$, $V_{DD} = 3.0 V$	-1.2	-1.0	-0.8	%/ $^{\circ}C$	2
		T_{EM5}^{*3} , $V_{DD} = 1.65 V$ to $5.5 V$	-1.26	-1.0	-0.76	%/ $^{\circ}C$	2
Oscillation frequency	f_{OSC}	$T_a = T_{SP5}$, $V_{DD} = 3.0 V$	1950	2300	2650	Hz	2
		$V_{DD} = 1.65 V$ to $5.5 V$	1860	2300	2780	Hz	2
		$T_a = T_{EM5}$, $V_{DD} = 3.0 V$	1670	2300	3040	Hz	2

*1. Ddt(E): Actual duty ratio temperature sensitivity

*2. T_{SP5} : Temperature $5^{\circ}C$ higher than duty ratio change-start temperature T_s (Refer to **Table 12** for details)

*3. T_{EM5} : Higher temperature when measuring duty ratio temperature sensitivity (Refer to **Table 12** for details)

3. Product with duty ratio temperature sensitivity $Ddt(s) = -2 \%/^{\circ}C$

Table 8

($T_a = T_{SP5}$, $V_{DD} = 3.0 V$, $V_{SS} = 0 V$, $C_{FREQ} = 4.7 nF$, unless otherwise specified)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit	Test circuit
Duty ratio accuracy	Dsp5	$V_{DD} = 3.0 V$	84.0	90.0	96.0	%	2
		$V_{DD} = 1.65 V$ to $5.5 V$	82.0	90.0	98.0	%	2
Duty ratio temperature sensitivity	Ddt(E) ^{*1}	$T_a = T_{SP5}^{*2}$, $V_{DD} = 3.0 V$	-2.4	-2.0	-1.6	%/ $^{\circ}C$	2
		T_{EM5}^{*3} , $V_{DD} = 1.65 V$ to $5.5 V$	-2.52	-2.0	-1.52	%/ $^{\circ}C$	2
Oscillation frequency	f_{OSC}	$T_a = T_{SP5}$, $V_{DD} = 3.0 V$	1840	2160	2740	Hz	2
		$V_{DD} = 1.65 V$ to $5.5 V$	1750	2160	2600	Hz	2
		$T_a = T_{EM5}$, $V_{DD} = 3.0 V$	1560	2160	2850	Hz	2

*1. Ddt(E): Actual duty ratio temperature sensitivity

*2. T_{SP5} : Temperature $5^{\circ}C$ higher than duty ratio change-start temperature T_s (Refer to **Table 12** for details)

*3. T_{EM5} : Higher temperature when measuring duty ratio temperature sensitivity (Refer to **Table 12** for details)

4. Product with duty ratio temperature sensitivity $Ddt(s) = -3 \%/^{\circ}C$

Table 9

(Ta = T_{SP5}, V_{DD} = 3.0 V, V_{SS} = 0 V, C_{FREQ} = 6.8 nF, unless otherwise specified)

Items	Symbol	Conditions	Min.	Typ.	Max.	Unit	Test circuit
Duty ratio accuracy	Dsp5	V _{DD} = 3.0 V	76.0	85.0	94.0	%	2
		V _{DD} = 1.65 V to 5.5 V	73.0	85.0	97.0	%	2
Duty ratio temperature sensitivity	Ddt(E)*1	Ta = T _{SP5} *2, V _{DD} = 3.0 V	-3.6	-3.0	-2.4	%/°C	2
		T _{EM5} *3, V _{DD} = 1.65 V to 5.5 V	-3.78	-3.0	-2.28	%/°C	2
Oscillation frequency	f _{OSC}	Ta = T _{SP5} , V _{DD} = 3.0 V	1900	2240	2570	Hz	2
		V _{DD} = 1.65 V to 5.5 V	1810	2240	2700	Hz	2
		Ta = T _{EM5} , V _{DD} = 3.0 V	1620	2240	2950	Hz	2

*1. Ddt(E): Actual duty ratio temperature sensitivity

*2. T_{SP5}: Temperature 5°C higher than duty ratio change-start temperature T_s (Refer to **Table 12** for details)

*3. T_{EM5}: Higher temperature when measuring duty ratio temperature sensitivity (Refer to **Table 12** for details)

5. Product with duty ratio temperature sensitivity $Ddt(s) = -4 \%/^{\circ}C$

Table 10

(Ta = T_{SP5}, V_{DD} = 3.0 V, V_{SS} = 0 V, C_{FREQ} = 10 nF, unless otherwise specified)

Items	Symbol	Conditions	Min.	Typ.	Max.	Unit	Test circuit
Duty ratio accuracy	Dsp5	V _{DD} = 3.0 V	68.0	80.0	92.0	%	2
		V _{DD} = 1.65 V to 5.5 V	64.0	80.0	96.0	%	2
Duty ratio temperature sensitivity	Ddt(E)*1	Ta = T _{SP5} *2, V _{DD} = 3.0 V	-4.8	-4.0	-3.2	%/°C	2
		T _{EM5} *3, V _{DD} = 1.65 V to 5.5 V	-5.05	-4.0	-3.04	%/°C	2
Oscillation frequency	f _{OSC}	Ta = T _{SP5} , V _{DD} = 3.0 V	1730	2030	2330	Hz	2
		V _{DD} = 1.65 V to 5.5 V	1640	2030	2440	Hz	2
		Ta = T _{EM5} , V _{DD} = 3.0 V	1470	2030	2680	Hz	2

*1. Ddt(E): Actual duty ratio temperature sensitivity

*2. T_{SP5}: Temperature 5°C higher than duty ratio change-start temperature T_s (Refer to **Table 12** for details)

*3. T_{EM5}: Higher temperature when measuring duty ratio temperature sensitivity (Refer to **Table 12** for details)

■ Test Circuits

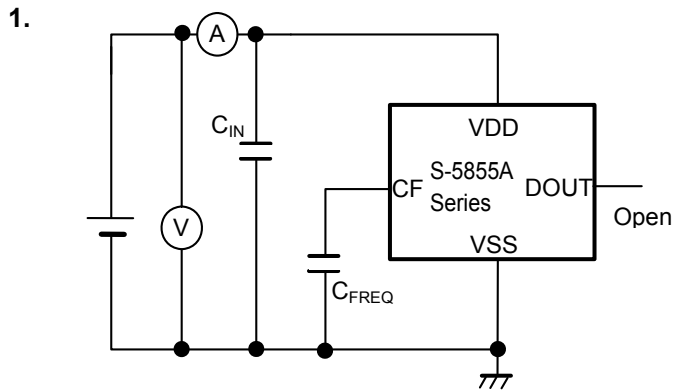
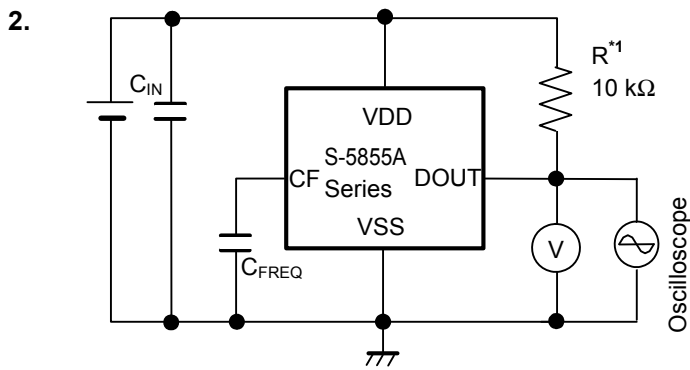


Figure 5



*1. Resistor (R) is unnecessary for the CMOS output product.

Figure 6

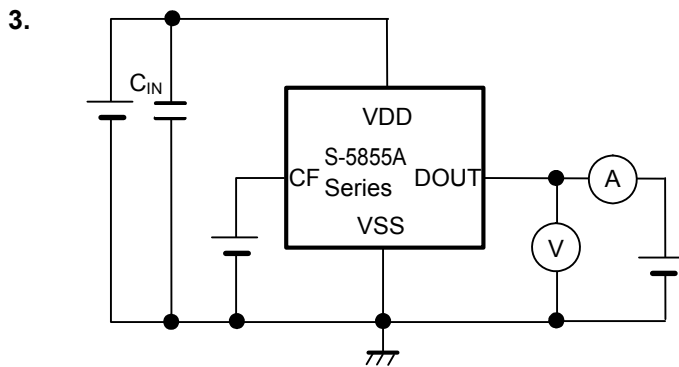


Figure 7

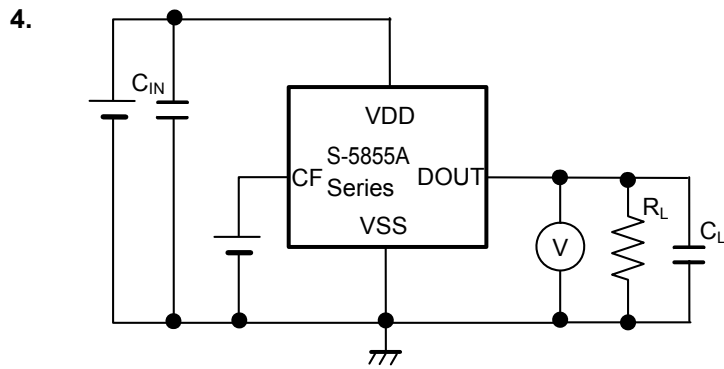


Figure 8

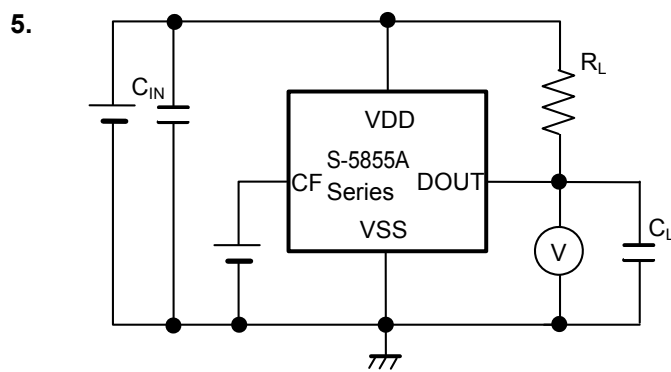
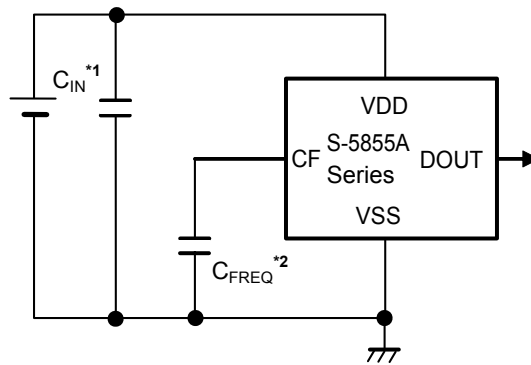


Figure 9

■ Standard Circuit



*1. C_{IN} is a capacitor for stabilization.

*2. C_{FREQ} is a capacitor for oscillation frequency.

Figure 10

Caution The above connection diagram and constant will not guarantee successful operation. Perform thorough evaluation using the actual application to set the constant.

■ Operation

1. Duty ratio

The following equation is the definition of duty ratio.

$$\text{Duty ratio} = \text{PW} / \text{T} \times 100 [\%]$$

The definitions of PW and T are shown in **Figure 11**.

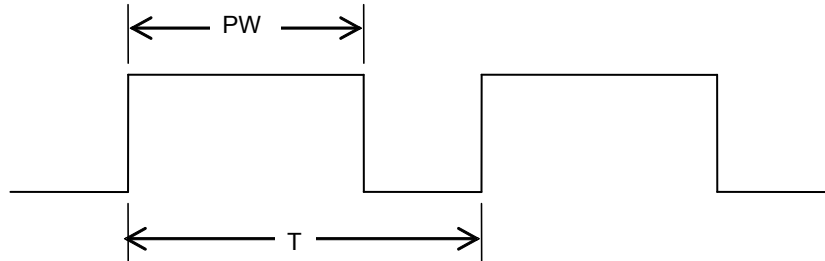


Figure 11

2. Oscillation frequency

The oscillation frequency is set by the capacitance value of the capacitor C_{FREQ} for the oscillation frequency.

The relationship between the C_{FREQ} capacitance value of each duty ratio temperature sensitivity and the center value of the oscillation frequency are shown in **Table 11**.

Table 11

Duty ratio temperature sensitivity Ddt(s) [%/°C]	C_{FREQ} capacitance value [nF]	Center value of oscillation frequency [Hz]
-1	2.2	2300
-2	4.7	2160
-3	6.8	2240
-4	10.0	2030

■ Explanation of Terms

1. Duty ratio accuracy (Dsp5)

Dsp5 shows duty ratio in temperature T_{SP5} 5°C higher than duty ratio change-start temperature T_s .

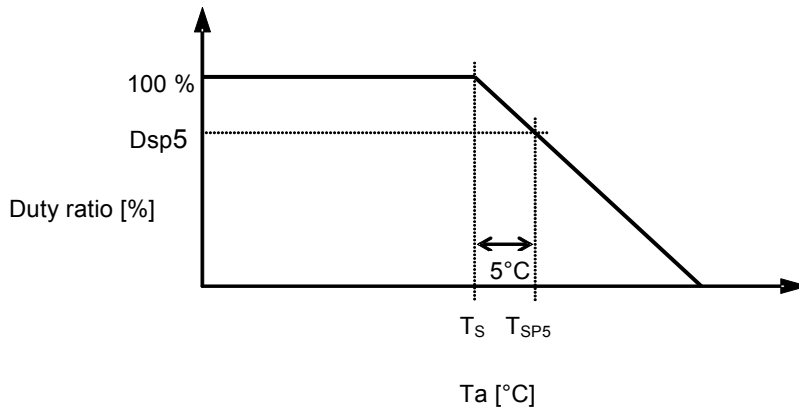
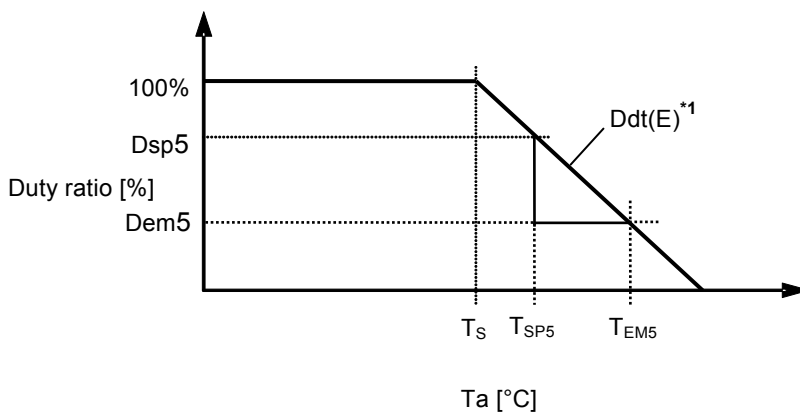


Figure 12

2. Duty ratio temperature sensitivity (Ddt(E))

Duty ratio temperature sensitivity (Ddt(E)) is the temperature coefficient of duty ratio calculated from the output duty ratio at $T_a = T_{SP5}$ and $T_a = T_{EM5}$. T_{EM5} is the temperature decided for each product shown in **Table 11**, and Dem5 is the output duty ratio at $T_a = T_{EM5}$. Ddt(E) is calculated using the following formula.

$$Ddt(E) = (Dem5 - Dsp5) / (T_{EM5} - T_{SP5}) \text{ [%/°C]}$$



*1. Selectable from -1 %/°C to -4 %/°C in 1 %/°C step

Figure 13

Table 12 T_{SP5} and T_{EM5} in Each Product

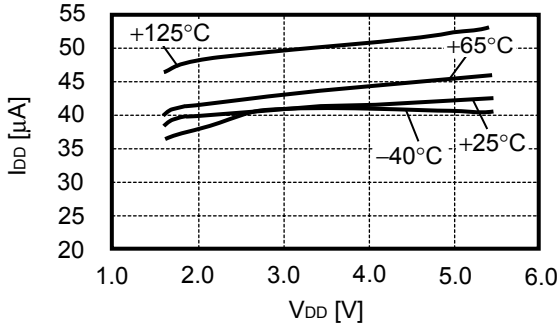
Duty ratio change-start temperature T _s [°C]	Duty ratio temperature sensitivity Ddt(s) [%/°C]	T _{SP5} [°C]	T _{EM5} [°C]
+40	-1	+45	+115
+40	-2	+45	+75
+40	-3	+45	+60
+40	-4	+45	+55
+50	-1	+55	+125
+50	-2	+55	+85
+50	-3	+55	+70
+50	-4	+55	+65
+60	-1	+65	+125
+60	-2	+65	+95
+60	-3	+65	+80
+60	-4	+65	+75
+70	-1	+75	+125
+70	-2	+75	+105
+70	-3	+75	+90
+70	-4	+75	+85
+80	-1	+85	+125
+80	-2	+85	+115
+80	-3	+85	+100
+80	-4	+85	+95

■ Precaution

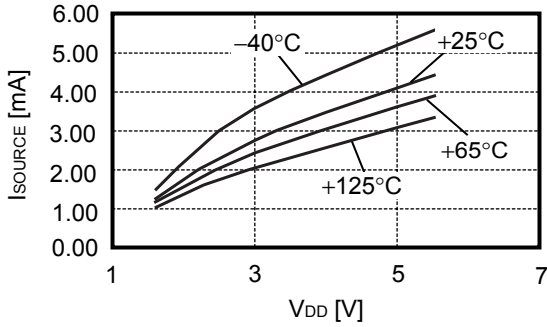
- Note that this IC may itself heat depending on a connected load to the output pin, resulting in error in measuring temperature.
- Set a capacitor (C_{IN}) of approx. 0.1 μ F between the VDD pin and VSS pin for stabilization as close to IC as possible.
- Connect a capacitor C_{FREQ} for oscillation frequency as close to IC as possible.
- Leakage current applied on the CF pin may cause error in the output duty ratio. Do not connect other components than C_{FREQ} .
- Since the error of the output duty ratio may become large depending on an application circuit or the design of a board pattern on this IC, perform thorough evaluation with the actually mounted model in the case of use.
- The application conditions for the input voltage, output voltage, and load current should not exceed the package power dissipation.
- Do not apply an electrostatic discharge to this IC that exceeds the performance ratings of the built-in electrostatic protection circuit.
- SII Semiconductor Corporation claims no responsibility for any disputes arising out of or in connection with any infringement by products, including this IC, of patents owned by a third party.

■ Characteristics (Typical Data)

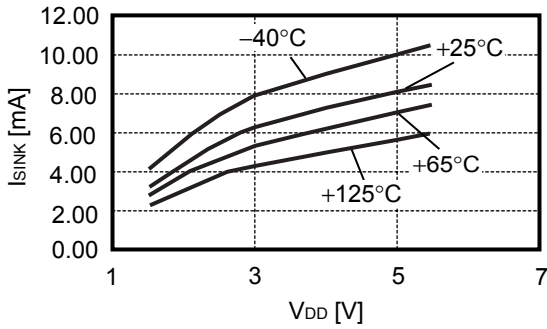
1. Current consumption (I_{DD}) vs. Power supply voltage (V_{DD})



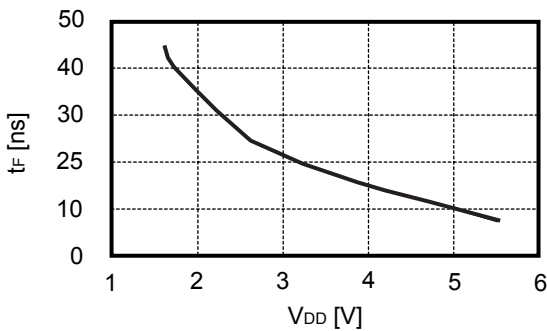
2. Output source current (I_{SOURCE}) vs. Power supply voltage (V_{DD})



3. Output sink current (I_{SINK}) vs. Power supply voltage (V_{DD})

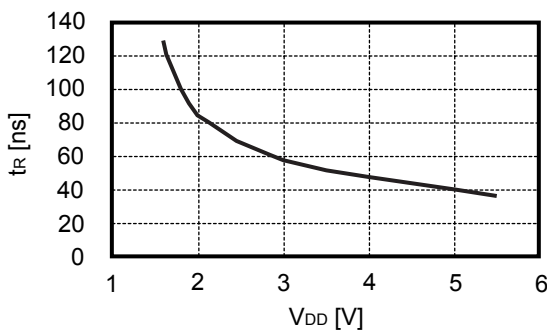


4. Fall time (t_F) vs. Power supply voltage (V_{DD}) dependency

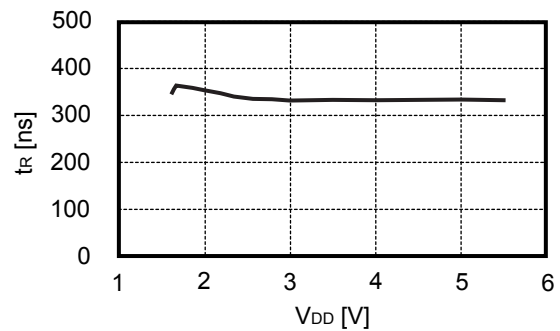


5. Rise time (t_R) vs. Power supply voltage (V_{DD}) dependency

5.1 CMOS output product

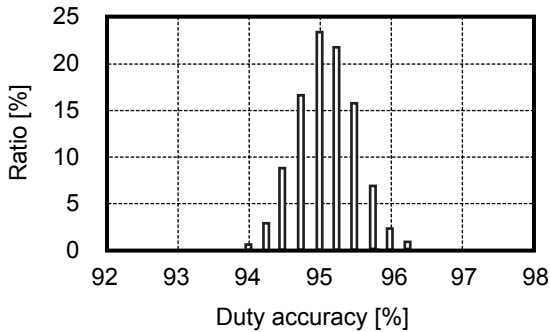


5.2 Nch open-drain output product

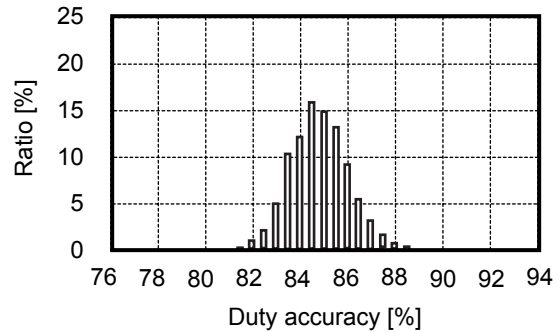


6. Duty ratio accuracy

6.1 Product with $T_a = T_{SP5}$, $Ddt(s) = -1\%/^{\circ}C$

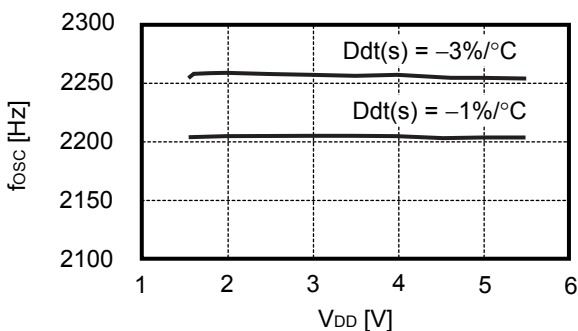


6.2 Product with $T_a = T_{SP5}$, $Ddt(s) = -3\%/^{\circ}C$

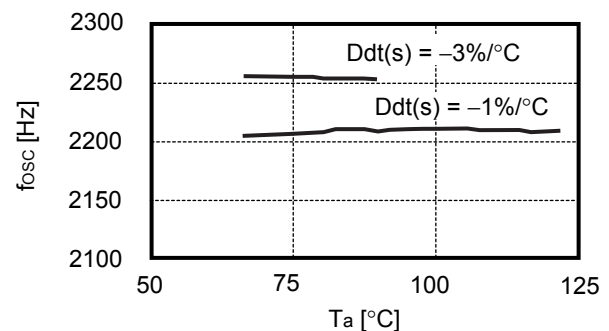


7. Oscillation frequency

7.1 Oscillation frequency (f_{osc}) vs. Power supply voltage (V_{DD})



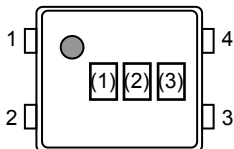
7.2 Oscillation frequency (f_{osc}) vs. Temperature (T_a)



■ Marking Specifications

(1) SNT-4A

SNT-4A
Top view



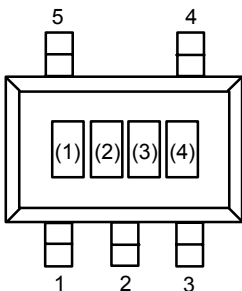
(1) to (3) : Product code (Refer to **Product name vs. Product code.**)

Product name vs. Product code

Product Name	Product Code		
	(1)	(2)	(3)
S-5855AACA-I4T1U	V	Q	C
S-5855AEAA-I4T1U	V	Q	Y
S-5855AECA-I4T1U	V	Q	3

(2) SOT-23-5

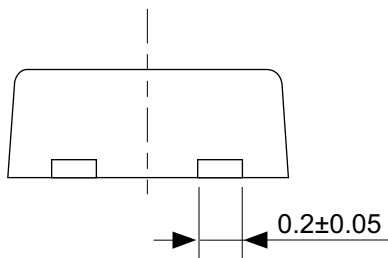
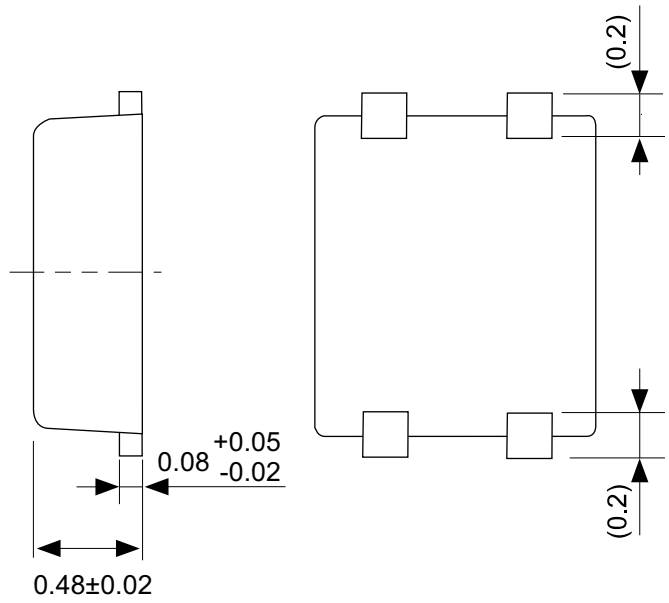
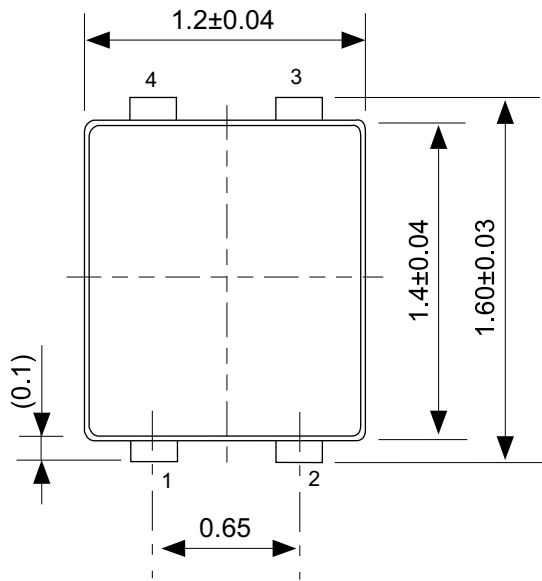
SOT-23-5
Top view



(1) to (3) : Product code (refer to **Product name vs. Product code**)
(4) : Lot number

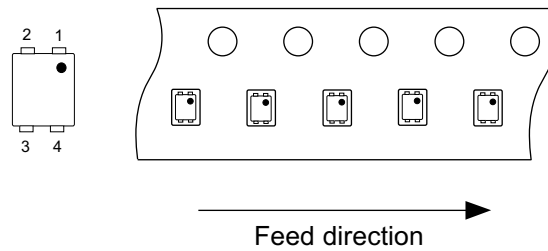
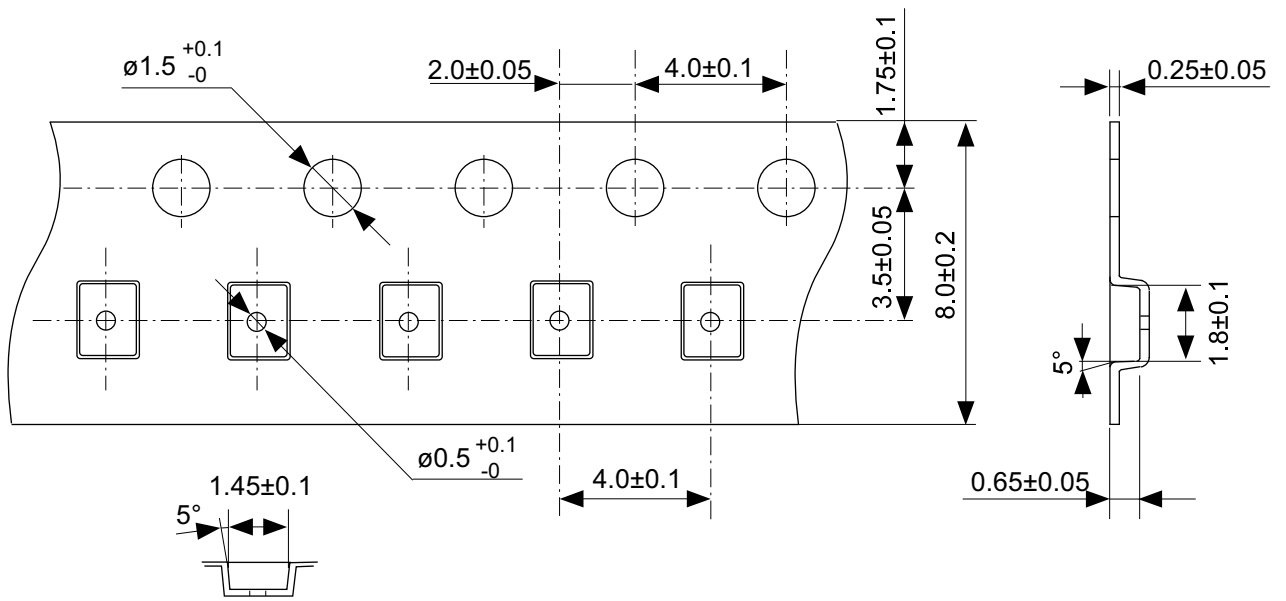
Product name vs. Product code

Product Name	Product Code		
	(1)	(2)	(3)
S-5855AAAA-M5T1U	V	Q	A
S-5855AAAB-M5T1U	V	R	A
S-5855AADA-M5T1U	V	Q	D



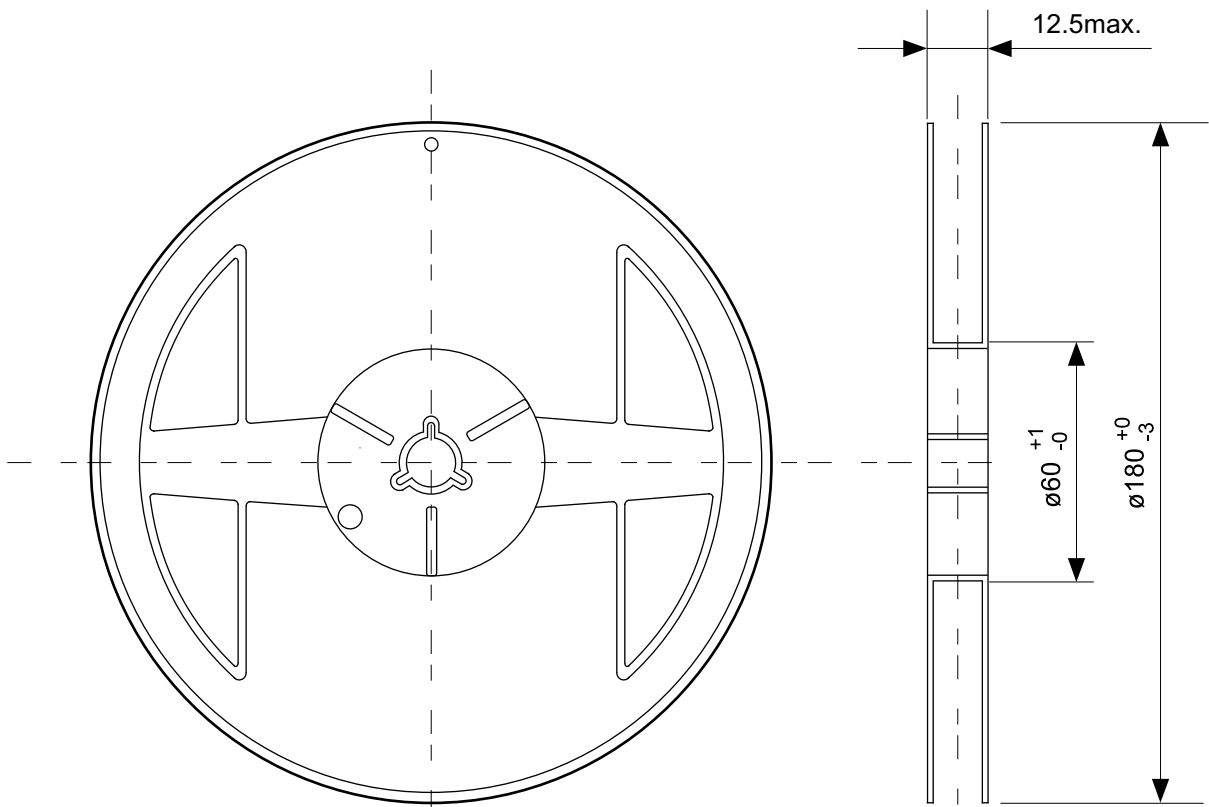
No. PF004-A-P-SD-4.0

TITLE	SNT-4A-A-PKG Dimensions
No.	PF004-A-P-SD-4.0
SCALE	
UNIT	mm
SII Semiconductor Corporation	

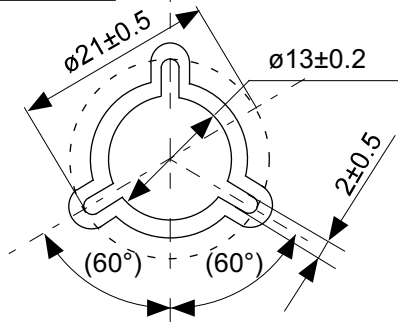


No. PF004-A-C-SD-1.0

TITLE	SNT-4A-A-Carrier Tape
No.	PF004-A-C-SD-1.0
SCALE	
UNIT	mm
SII Semiconductor Corporation	

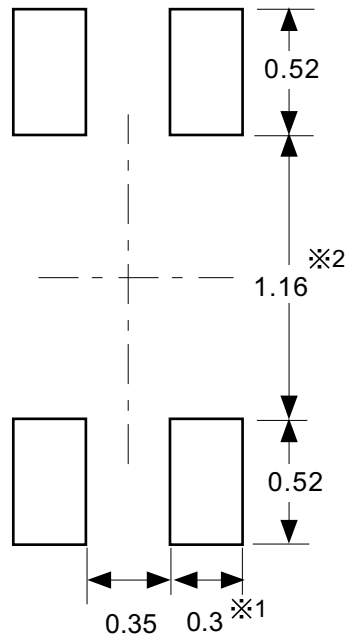


Enlarged drawing in the central part



No. PF004-A-R-SD-1.0

TITLE	SNT-4A-A-Reel		
No.	PF004-A-R-SD-1.0		
SCALE		QTY.	5,000
UNIT	mm		
SII Semiconductor Corporation			



※1. ランドパターンの幅に注意してください (0.25 mm min. / 0.30 mm typ.).

※2. パッケージ中央にランドパターンを広げないでください (1.10 mm ~ 1.20 mm)。

- 注意
1. パッケージのモールド樹脂下にシルク印刷やハンダ印刷などしないでください。
 2. パッケージ下の配線上のソルダーレジストなどの厚みをランドパターン表面から0.03 mm 以下にしてください。
 3. マスク開口サイズと開口位置はランドパターンと合わせてください。
 4. 詳細は "SNTパッケージ活用の手引き" を参照してください。

※1. Pay attention to the land pattern width (0.25 mm min. / 0.30 mm typ.).

※2. Do not widen the land pattern to the center of the package (1.10 mm to 1.20 mm).

- Caution**
1. Do not do silkscreen printing and solder printing under the mold resin of the package.
 2. The thickness of the solder resist on the wire pattern under the package should be 0.03 mm or less from the land pattern surface.
 3. Match the mask aperture size and aperture position with the land pattern.
 4. Refer to "SNT Package User's Guide" for details.

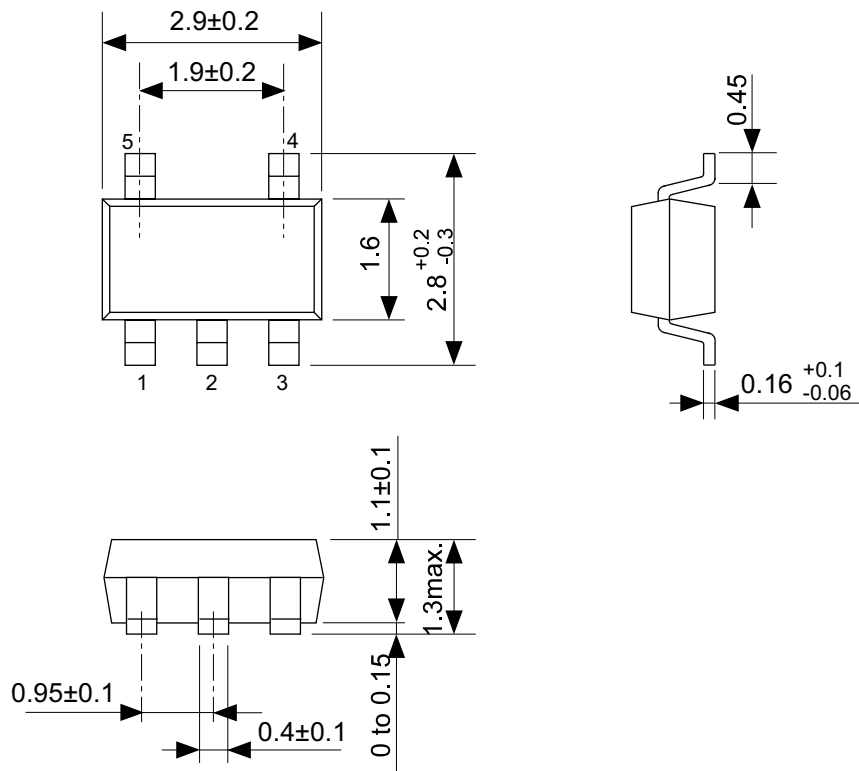
※1. 请注意焊盘模式的宽度 (0.25 mm min. / 0.30 mm typ.).

※2. 请勿向封装中间扩展焊盘模式 (1.10 mm ~ 1.20 mm)。

- 注意
1. 请勿在树脂型封装的下面印刷丝网、焊锡。
 2. 在封装下、布线上的阻焊膜厚度 (从焊盘模式表面起) 请控制在 0.03 mm 以下。
 3. 钢网的开口尺寸和开口位置请与焊盘模式对齐。
 4. 详细内容请参阅 "SNT 封装的应用指南"。

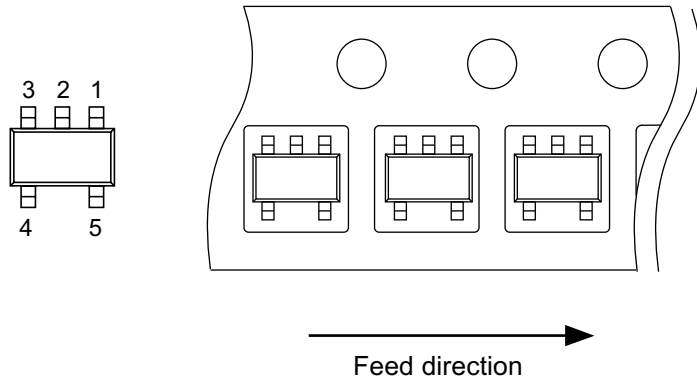
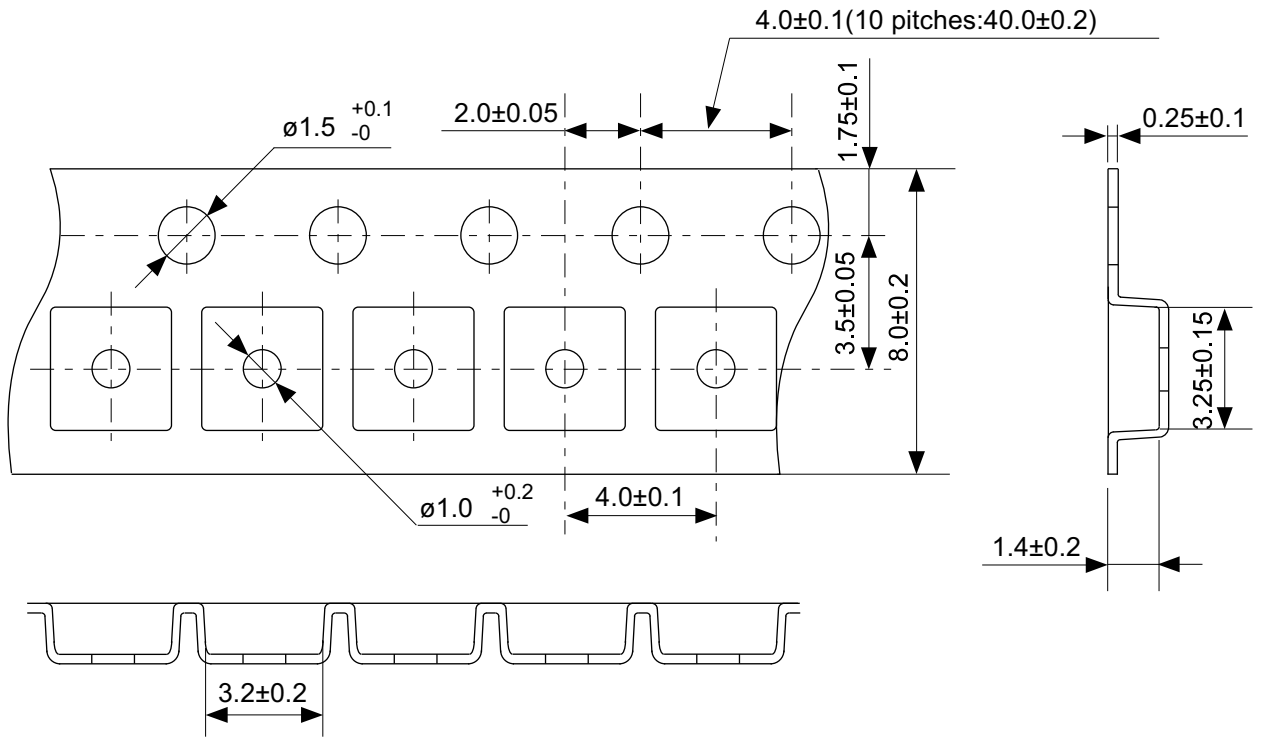
No. PF004-A-L-SD-4.1

TITLE	SNT-4A-A -Land Recommendation
No.	PF004-A-L-SD-4.1
SCALE	
UNIT	mm
SII Semiconductor Corporation	



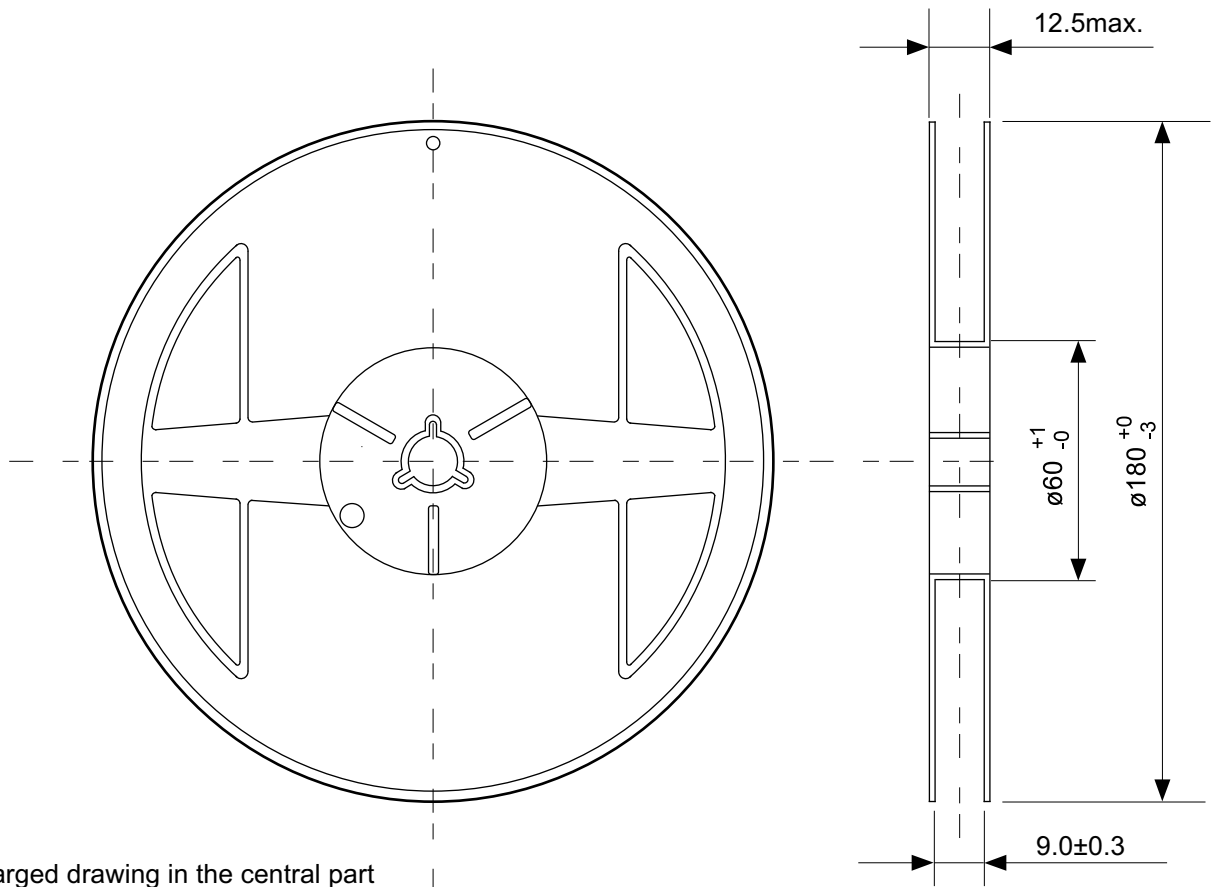
No. MP005-A-P-SD-1.2

TITLE	SOT235-A-PKG Dimensions
No.	MP005-A-P-SD-1.2
SCALE	
UNIT	mm
SII Semiconductor Corporation	

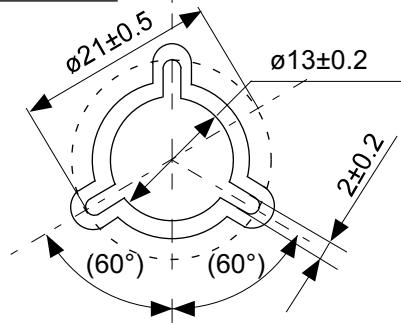


No. MP005-A-C-SD-2.1

TITLE	SOT235-A-Carrier Tape
No.	MP005-A-C-SD-2.1
SCALE	
UNIT	mm
SII Semiconductor Corporation	



Enlarged drawing in the central part



No. MP005-A-R-SD-1.1

TITLE	SOT235-A-Reel		
No.	MP005-A-R-SD-1.1		
SCALE		QTY.	3,000
UNIT	mm		
SII Semiconductor Corporation			

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